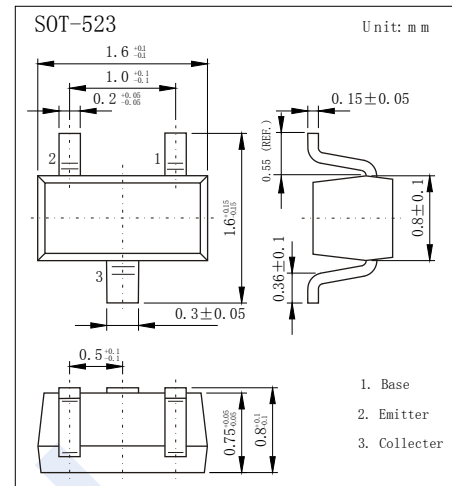


PNP Transistors

2SA1832

■ Features

- High voltage and high current
- Excellent hFE linearity
- Complementary to 2SC4738

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V_{CBO}	-50	V
Collector - Emitter Voltage	V_{CEO}	-50	
Emitter - Base Voltage	V_{EBO}	-5	
Collector Current - Continuous	I_C	-150	mA
Collector Power Dissipation	P_C	100	mW
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	125	$^\circ\text{C/W}$
Junction Temperature	T_J	125	$^\circ\text{C}$
Storage Temperature range	T_{stg}	-65 to 125	

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	V_{CBO}	$I_C = -100 \mu\text{A}, I_E = 0$	-50			V
Collector- emitter breakdown voltage	V_{CEO}	$I_C = -1 \text{ mA}, I_B = 0$	-50			
Emitter - base breakdown voltage	V_{EBO}	$I_E = -100 \mu\text{A}, I_C = 0$	-5			
Collector-base cut-off current	I_{CBO}	$V_{CB} = -50 \text{ V}, I_E = 0$			-100	nA
Emitter cut-off current	I_{EBO}	$V_{EB} = -5 \text{ V}, I_C = 0$			-100	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -100 \text{ mA}, I_B = -10 \text{ mA}$		-0.1	-0.3	V
Base - emitter saturation voltage	$V_{BE(sat)}$	$I_C = -100 \text{ mA}, I_B = -10 \text{ mA}$			-1.2	
DC current gain	hFE	$V_{CE} = -6 \text{ V}, I_C = -2 \text{ mA}$	70		400	
Collector output capacitance	C_{ob}	$V_{CB} = -10 \text{ V}, I_E = 0 \text{ mA}, f = 1 \text{ MHz}$		4	7	pF
Transition frequency	f_T	$V_{CE} = -10 \text{ V}, I_C = -1 \text{ mA}$	80			MHz

■ Classification of hfe

Type	2SA1832-O	2SA1832-Y	2SA1832-G
Range	70-140	120-240	200-400
Marking	SO	SY	SG

PNP Transistors

2SA1832

■ Typical Characteristics

